# EECS 151/251A Homework 11

Due 11:59pm Friday, December  $3^{\rm rd},\,2021$ 

# 1 Memory Implementation

Suppose you want to design a 32-bit wide byte-addressable memory block with a capacity of 2K 32-bit words of storage (1K = 1024). Besides, we would like to make the memory block has a 1:1 aspect ratio (equal number of rows and columns).

<b>a</b> ]	How many rows and columns of SRAM cells are there in your design?
	$(row) \times (column)$
	How many total address bits do you need for this memory? How many address bits are used he row-decoder? How many address bits are used by the column-decoder?
It no	eeds bits address
	bits are used by row-decoder
	bits are used by column-decoder

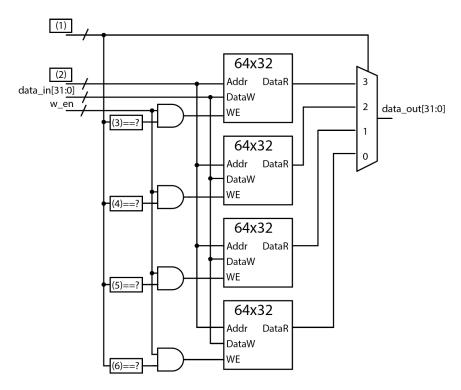
### 2 Building Bigger Blocks

As modern processors can handle more and more computations per second, the associated memories must also hold more and more data to keep up. However, one major problem with making huge SRAM blocks is that the bit lines will become extremely long as the memory increases in capacity, which causes issues with readability and write speed. One way to get around this problem is to make the overall memory block out of smaller sub-blocks.

$\mathbf{a}$	For this problem, you only have access to an SRAM block that is 32 words deep with a 16-bit
wo	rd length. The basic SRAM block has a single read port and a single write port. Suppose you
wa	nt to design a 32-bit wide memory block with a capacity of 2K 32-bit words of storage, and we
wil	l still want to stick to a 1:1 aspect ratio. How many rows and columns of this small SRAM
blo	ocks are there in your design?

(row)	) ×	(column)

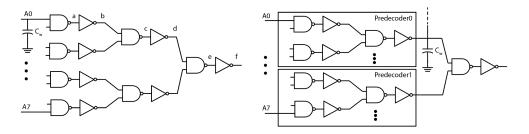
**b** Now you are given a memory block that is  $64 \times 32$  and supposes you want to use multiple instances to design a  $256 \times 32$  memory. The diagram below is a possible implementation. Fill the address signal names in the blanks and use the little-endian convention. For the blanks at the input of AND gates, fill in the decoded result. (==00, 01, 10 or 11)



- 1.
- 2.
- 3.
- 4.
- 5.
- 6.

#### 3 Memory decoder

Now we want to design the row decoder for an SRAM that has 256 rows. We will compare the decoding with and without the pre-decoder technique presented in the lecture. We will only use 2-input gates and inverters. Each word line has 256 cells. And the capacitance  $C_{cell}$  for each cell includes the transistor and wire capacitance.



a What are the total fanout, branching effort, and path logical effort for each address wire? Here we assume the decoder input capacitance. In this question, we ignore the wire capacitance  $C_w$  in the diagram and we assume the input capacitance for each address is  $C_{address} = C_{in}$  and also  $C_{in} = 4C_{cell}$ 

$$H=$$

**b** Now we use the pre-decoder technique presented in the lecture slides. For the total 8-bit address, we use two 4-bit pre-decoder. And the final decoder is an AND2 gate. We still assume  $C_{address} = C_{in}$  and  $C_{in} = 4C_{cell}$ . What are the total fanout, branching effort, and path logical effort for each address wire? In this question, we also ignore the wire capacitance  $C_w$  in the diagram.

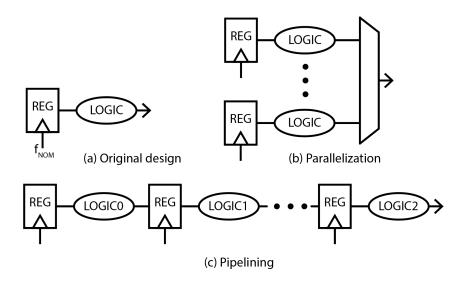
$$H=$$

$$G=$$

c (251 only) What is the optimum number of stages for these two cases? Round up the result to an integer.
The optimum number of stage without predecoder is:
The optimum number of stage with predecoder is:
<b>d</b> We want to investigate the switching activity at each node. Now assume all the address inputs (A0-A7) have the same possibility equal 1 or 0 ( $P(A_i = 1) = 1/2$ ). Determine the activity factor $\alpha_{0\to 1}$ (the possibility of one node changes from 0 to 1) of each node in the 8-input AND gate decoder.
$\bullet$ $\alpha_a =$
$\bullet$ $\alpha_b =$
$\bullet$ $\alpha_c =$
$\bullet$ $\alpha_d =$
$\bullet$ $\alpha_e =$
$\bullet$ $\alpha_f =$
e (251 only) Under the same assumption of question (d), consider the long address wire capacitance $C_w$ in the circuit above. Assume the SRAM is consistently read by a clock with frequency $f_{clk}$ . And the SRAM connects to supply $V_{dd}$ . What is the power that it spends on one of those long wires? Provide your answer in terms of $f_{clk}$ , $V_{dd}$ , $C_w$
For the decoder without pre-decoding technique
For the decoder using pre-decoders

### 4 Parallelism and Pipelining

In this problem, we will look into low power design tradeoffs. You are given the logic block is shown below, which, at nominal supply voltage  $V_{DD,NOM}$  runs at frequency  $f_{NOM}$ . You may assume that the logic block has total average capacitance  $C_{logic}$  (average capacitance defined as the product of activity factor  $\alpha_{0\to 1}$  and total load capacitance  $C_L$ ), the register block has average capacitance  $C_{reg}$ . The delay of a register (i.e., setup time, clk-to-Q, etc.) is negligible compared to the logic delay of the path. After analyzing your circuit you determined that the delay of the logic block can be simplified using a linear approximation:  $t_d \propto \frac{1}{V_{DD}}$ 



**a** Derive an expression for the dynamic power  $(P_{NOM})$  dissipated in the circuit at nominal operating conditions. Provide your anwser in terms of  $V_{DD,NOM}$ ,  $f_{NOM}$ ,  $C_{logic}$ ,  $C_{reg}$ .



b You decide to exploit N-times parallelization (N parallel paths) to decrease the power dissipation of your design while maintaining the same throughput. An N-input multiplexer with average capacitance  $C_{MUX,data}$  at each data input, and average capacitance  $C_{MUX,sel}$  at each select input has to be used in order to reserialize the parallel paths back to a single stream. What is the clock frequency of the registers and the data and control inputs of the MUX? What is the supply voltage you will use in terms of the nominal values and N? Note that you can assume that the delay of the